


## INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.2343-02	Div. of Appln. No.	<del>10/200,446</del> 10810837
Applicant	Atsushi YAGISHITA et al.		
Filing Date	Herewith	Prior Group:	2823

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Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
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Examiner		Date Considered	2/1/06
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